

3 A Ultra Low Current Consumption N-channel Load Switch with Lower Input Voltage Range and Reverse Current Blocking

**Product Specification** 

#### **DESCRIPTION**

The GLF72510 / GLF72511 Load Switch is a fully integrated 2A NMOS load switch with  $I_QSmart^{TM}$  advanced technology. The device is targeted for the mobile computing and data storage markets as a high performance, low cost solution for load switch applications.

The GLF72510 / GLF72511 has a constant low on-resistance of 27 m $\Omega$  at room temperature. The fixed rise time helps prevent undesirable inrush current when turned on and the internal EN pin pulldown resistor ensures the device remains in the shutdown mode when disabled. In shutdown mode the GLF72510 / GLF72511 draws only 6 nA typical at 3.6 V input supply voltage.

The GLF72510 / GLF72511 is available in a wafer level chip scale package (WLCSP) measuring 0.97 mm x 0.97 mm x 0.55mm with a 0.5 mm pitch. This allows the user to save board space and increase cost savings.

The GLF72510 / GLF72511 features a reverse current blocking protection. When the GLF72510 / GLF72511 is disabled, it prevents reverse current flowing from the output to the input source.

#### **FEATURES**

Supply Voltage Range: 0.8 V to 3.6 V

• Low Ron: 27 mΩ Typ at Supply Voltage Range

lout Max : 3 AUltra-Low lo :

50 nA Typ at 0.8 V<sub>IN</sub>

60 nA Typ at 1.0 V<sub>IN</sub>

80 nA Typ at 1.2 V<sub>IN</sub>

Integrated Slew Rate Control Driver

Reverse Current Blocking Protection When Disabled

Internal EN Pull-Down Resistor

Integrated Output Discharge Switch: GLF72511

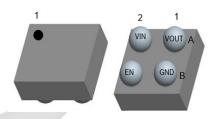
• HBM: 6 kV, CDM: 2 kV

 Ultra-Small: 0.97mm x 0.97mm x 0.55mm Wafer Level Chip Scale Package

#### **APPLICATIONS**

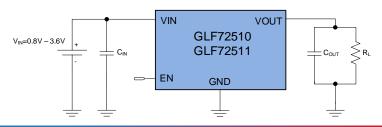
- Wearables
- Data Storage, SSD
- Low Power Subsystems

#### **PACKAGE**



0.97 mm x 0.97 mm x 0.55 mm WLCSP

#### **APPLICATION DIAGRAM**



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#### **ALTERNATE DEVICE OPTIONS**

Part Number	Top Mark	R <sub>ON</sub> (Typ) at 3.6 V	Output Discharge	EN Activity
GLF72510	СР	27 mΩ	No	High
GLF72511	CQ	27 mΩ	Yes	High

#### **FUNCTIONAL BLOCK DIAGRAM**

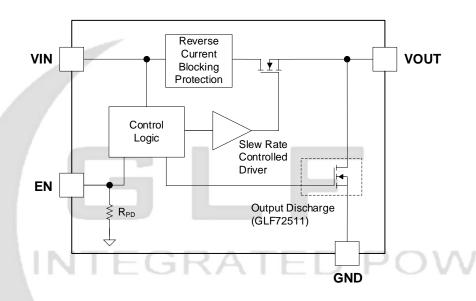


Figure 1. Functional Block Diagram

**PIN DEFINITION** 

#### **PIN CONFIGURATION**

Top View

# 1 2 1 Pin # VIN VOUT A A1

GND B

**Bottom View** 

Figure 2. 0.97mm x 0.97mm x 0.55mm WLCSP

Pin#	Name	Description
A1	Vouт	Switch Output
A2	VIN	Switch Input. Supply Voltage for IC
B1	GND	Ground
B2	EN	Enable to control the switch



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#### **ABSOLUTE MAXIMUM RATINGS**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Par	Min.	Max.	Unit	
V <sub>IN</sub>	V <sub>IN</sub> , V <sub>OUT</sub> , V <sub>EN</sub> to GND			4	V
Іоит	Maximum Continuous Switch Current			3	Α
PD	Power Dissipation at T <sub>A</sub> = 25°C		1.2	W	
Tstg	Storage Junction Temperature	-65	150	°C	
TA	Operating Temperature Range	-40	85	°C	
$\theta_{JA}$	Thermal Resistance, Junction to Ambient			85	°C/W
ESD	Flactrostatia Discharge Canability	Human Body Model, JESD22-A114	6		14) /
ESD	Electrostatic Discharge Capability  Charged Device Model, JESD22-C101		2		kV

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min.	Max.	Unit
V <sub>IN</sub>	Supply Voltage	0.8	3.6	V
TA	Ambient Operating Temperature	-40	+85	°C

#### **ELECTRICAL CHARACTERISTICS**

 $V_{IN}$  = 0.8 V to 3.6 V and  $T_A$  = 25 °C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units		
Basic Ope	ration			1	•			
		EN = Enable, I <sub>OUT</sub> = 0 mA, V <sub>IN</sub> = 0.8 V	50					
		EN = Enable, I <sub>OUT</sub> = 0 mA, V <sub>IN</sub> = 1.0 V		60		nΑ		
		EN = Enable, I <sub>OUT</sub> = 0 mA, V <sub>IN</sub> = 1.2 V		80		7		
	Ovices and Oversent	EN = Enable, I <sub>OUT</sub> = 0 mA, V <sub>IN</sub> = 2.5 V		3				
lα	Quiescent Current	EN = Enable, I <sub>OUT</sub> = 0 mA, V <sub>IN</sub> = 3.0 V		8				
		EN = Enable, I <sub>OUT</sub> = 0 mA, V <sub>IN</sub> = 3.3 V		10		uA		
		EN = Enable, I <sub>OUT</sub> = 0 mA, V <sub>IN</sub> = 3.6 V		15				
		EN = Enable, I <sub>OUT</sub> = 0 mA, V <sub>IN</sub> = 3.6 V, Ta = 85 °C		29				
		EN = Disable, I <sub>OUT</sub> = 0 mA, V <sub>IN</sub> = 0.8 V		2		nA		
	Shutdown Current	EN = Disable, I <sub>OUT</sub> = 0 mA, V <sub>IN</sub> = 1.0 V		2				
		EN = Disable, I <sub>OUT</sub> = 0 mA, V <sub>IN</sub> = 1.2 V		3				
		EN = Disable, I <sub>OUT</sub> = 0 mA, V <sub>IN</sub> = 2.5 V		4				
I <sub>SD</sub>		EN = Disable, I <sub>OUT</sub> = 0 mA, V <sub>IN</sub> = 3.0 V		5				
		EN = Disable, I <sub>OUT</sub> = 0 mA, V <sub>IN</sub> = 3.3 V		5				
		EN = Disable, I <sub>OUT</sub> = 0 mA, V <sub>IN</sub> = 3.6 V		6	15			
	The same of	EN = Disable, I <sub>OUT</sub> = 0 mA, V <sub>IN</sub> = 3.6 V, Ta = 85 °C		470	550			
Б		V <sub>IN</sub> = 0.8 V to 3.6 V Ta = 25 °C		27	33			
Ron	On-Resistance	lо⊔т = 300 mA		35	40	mΩ		
.,		V <sub>IN</sub> = 0.8 V - 1.5 V	0.8			٧		
ViH	EN Input Logic High Voltage	V <sub>IN</sub> = 1.5 V – 3.6 V				V		
.,	EN Insuit I seis I sur Valtana	V <sub>IN</sub> = 0.8 V – 1.5 V			0.2	V		
VIL	EN Input Logic Low Voltage	V <sub>IN</sub> = 1.5 V – 3.6 V			0.5	V		
R <sub>EN</sub>	EN pull down resistance	Internal Resistance		10		МΩ		
Rosc	Output Discharge Resistance (1)	GLF72511, EN = GND		85		Ω		

Notes: 1. Output discharge path is disabled when main switch is off.

#### **ELECTRICAL CHARACTERISTICS**

 $V_{IN} = 0.8 \text{ V}$  to 3.6 V and  $T_A = 25 \,^{\circ}\text{C}$  unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units		
Switching Characteristics (2)								
		V <sub>IN</sub> = 0.8 V		470				
	Turn-On Delay	V <sub>IN</sub> = 1.2 V		270				
t <sub>dON</sub>	$R_{OUT} = 150 \Omega$ , $C_{OUT} = 0.1 \mu F$	V <sub>IN</sub> = 3.3 V		150				
		V <sub>IN</sub> = 3.6 V		140				
		V <sub>IN</sub> = 0.8 V		490				
	$V_{OUT}$ Rise Time Rout = 150 Ω, Cout = 0.1 μF	V <sub>IN</sub> = 1.2 V		480				
t <sub>R</sub>		V <sub>IN</sub> = 3.3 V		420		μs		
		V <sub>IN</sub> = 3.6 V		430		μο		
		V <sub>IN</sub> = 0.8 V		80				
_	Turn-Off Delay $R_{OUT} = 150 \Omega$ , $C_{OUT} = 0.1 \mu F$	V <sub>IN</sub> = 1.2 V		5				
t <sub>dOFF</sub>		V <sub>IN</sub> = 3.3 V		2				
	LINITE	V <sub>IN</sub> = 3.6 V		Λ1/1				
A	111/11/1	V <sub>IN</sub> = 0.8 V		30				
	V <sub>OUT</sub> Fall Time, GLF72510	V <sub>IN</sub> = 1.2 V		30				
	R <sub>OUT</sub> = 150 Ω, C <sub>OUT</sub> = 0.1 μF	V <sub>IN</sub> = 3.3 V		30				
t⊧		V <sub>IN</sub> = 3.6 V		30				
		V <sub>IN</sub> = 0.8 V		24				
	V <sub>OUT</sub> Fall Time, GLF72511	V <sub>IN</sub> = 1.2 V		14				
	Rout = 150 Ω, Cout = 0.1 μF	V <sub>IN</sub> = 3.3 V		11				
		V <sub>IN</sub> = 3.6 V		12				

Notes: 2. By design; characterized, not production tested.  $t_{ON} = t_{dON} + t_{R}$ ,  $t_{OFF} = t_{dOFF} + t_{F}$ 

#### **TIMING DIAGRAM**

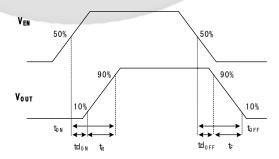


Figure 3. Timing Diagram

#### TYPICAL PERFORMANCE CHARACTERISTICS

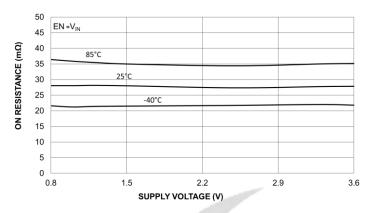


Figure 1. On-Resistance vs. Supply Voltage

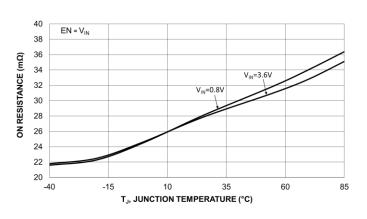


Figure 2. On-Resistance vs. Temperature

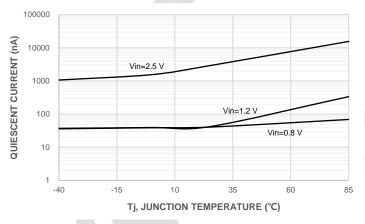


Figure 3. Quiescent Current vs. Temperature

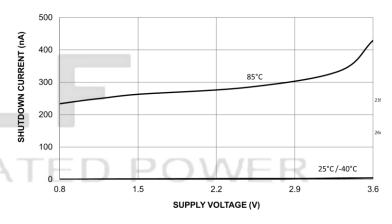


Figure 7. Shutdown Current vs. Supply Voltage

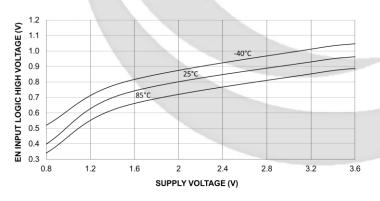


Figure 8. EN Input Logic High Threshold

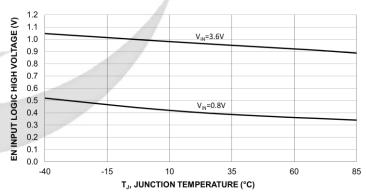
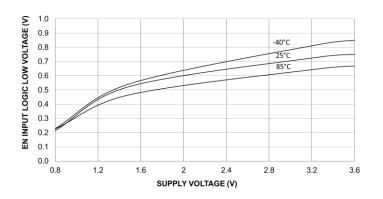


Figure 9. EN Input Logic High Threshold Vs. Temperature

# CIE

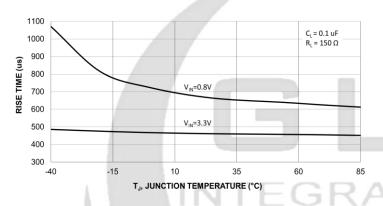
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INPUT LOGIC LOW THRESHOLD (V) 1.1 1.0 0.9 V<sub>IN</sub>=3.6V 0.8 0.7 0.5 0.4 0.3 V<sub>IN</sub>=0.8V 0.2 0.1 Ë 0.0 -15 60 85 T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

Figure 40. EN Input Logic Low Threshold

Figure 51. EN Input Logic Low Threshold Vs. Temperature



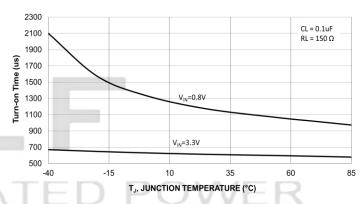
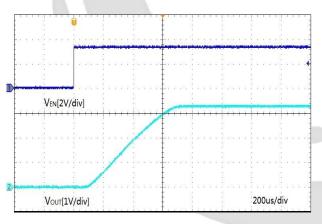


Figure 12. Vout Rise Time vs. Temperature

Figure 63. Turn-On Time vs. Temperature



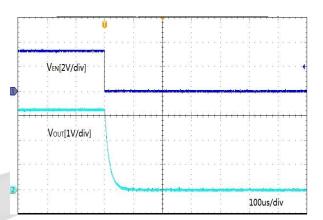


Figure 14. Turn-On Response  $V_{\text{IN}} = 3.3 \text{ V, } C_{\text{OUT}} = 0.1 \text{ uF, } R_{\text{L}} = 150 \text{ }\Omega$ 

Figure 75. Turn-Off Response, GLF72511  $V_{IN} = 3.3 \text{ V}, C_{OUT} = 0.1 \text{ uF}, R_L = 150 \Omega$ 



#### APPLICATION INFORMATION

The GLF72510 / GLF72511 is a fully integrated 3 A NMOS load switch with fixed slew rate control to limit the inrush current during turn on. Each device is capable of operating over a wide input range from 0.8 V to 3.6 V with very low on-resistance to reduce conduction loss. In the off state, these devices consume very low leakage current, avoiding unwanted standby current from the input power supply. The GLF72510 is available in the 0.97 mm x 0.97 mm x 0.55mm wafer level chip scale package with four bumps at 0.5 mm pitch to save space in compact applications.

#### **Input Capacitor**

A capacitor is recommended to be placed close to the  $V_{IN}$  pin to reduce the voltage drop on the input power rail caused by transient inrush current at start-up. A higher input capacitor value can be used to further attenuate the input voltage drop.

#### **Output Capacitor**

An output capacitor is recommended to minimize voltage undershoot on the output pin during the transition when the switch is turned off. Undershoot can be caused by parasitic inductance from board traces or intentional load inductances. If load inductances do exist, use of an output capacitor can improve output voltage stability and system reliability. The C<sub>OUT</sub> capacitor should be placed close to the VOUT and GND pins.

#### **Reverse Current Blocking**

The GLF72510 / GLF72511 has a built-in reverse current blocking protection. When the device is disabled, the reverse current blocking protection is activated to prevent the reverse current from the Vout to the Vin source.

#### EN pin

The GLF72510 / GLF72511 can be activated by EN pin high. Note that the EN pin has an internal pull-down resistor to maintain a reliable status without EN signal applied from an external controller.

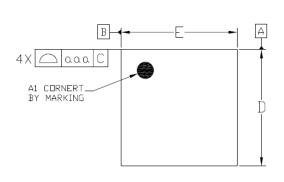
#### **Output Discharge Function**

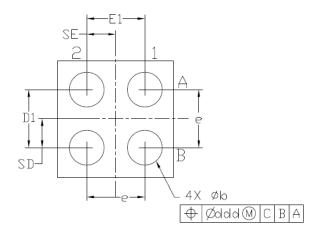
The GLF72511 has an internal discharge N-channel FET switch on the VOUT node. When EN signal turns the main power FET to an off state, the N-channel switch turns on to discharge an output capacitor quickly.

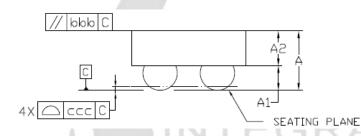
#### **Board Layout**

All traces should be as short as possible to minimize parasitic inductance effect. Wide traces for VIN, VOUT, and GND will help reduce signal degradation and parasitic effects during dynamic operations as well as improve the thermal performance at high load current.

#### **PACKAGE OUTLINE**







	Dimensional Ref.									
REF.	Min.	Nom.	Max.							
А	0.500	0.550	0.600							
Α1	0.225	0.250	0.275							
Α2	0.275	0.300	0.325							
D	0.960	0.970	0.985							
Е	0.960	0.970	0.985							
D1	0.450	0.500	0.550							
E1	0.450	0.500	0.550							
Ь	0.260	0.310	0.360							
е	0	.500 BS	C							
SD	0	.250 BS	C							
SE	0	.250 BS	C							
To	Tol. of Form&Position									
999	0.10									
bbb	0.10									
CCC	0.05									
ddd		0.05								

## Notes

- 1. ALL DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
- 2. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.

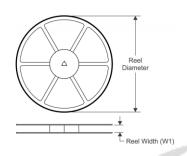


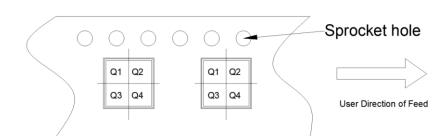
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#### TAPE AND REEL INFORMATION

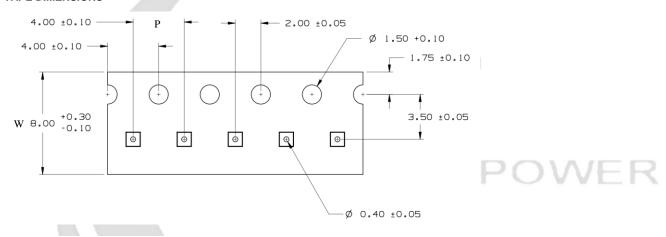
#### REEL DIMENSIONS

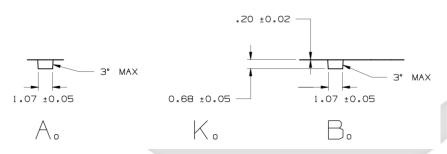
#### **QUADRANT ASSIGNMENTS PIN 1 ORIENTATION TAPE**





#### **TAPE DIMENSIONS**





Device	Package	Pins	SPQ	Reel Diameter(mm)	Reel Width W1	Α0	В0	K0	Р	W	Pin1
GLF72510	WLCSP	4	3000	180	9	1.07	1.07	0.68	4	8	Q1
GLF72511	WLCSP	4	3000	180	9	1.07	1.07	0.68	4	8	Q1

#### Remark:

- A0: Dimension designed to accommodate the component width
- B0: Dimension designed to accommodate the component length
- C0: Dimension designed to accommodate the component thickness
- W: Overall width of the carrier tape
- P: Pitch between successive cavity centers



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#### SPECIFICATION DEFINITIONS

Document Type	Meaning	Product Status
Target Specification	This is a target specification intended to support exploration and discussion of critical needs for a proposed or target device. Spec limits including typical, minimum, and maximum values are desired, or target, limits. GLF reserves the right to change limits at any time without warning or notification. A target specification in no way guarantees future production of the device in question.	Design / Development
Preliminary Specification	This is a draft version of a product specification. The specification is still under internal review and subject to change. GLF reserves the right to change the specification at any time without warning or notification. A preliminary specification in no way guarantees future production of the device in question.	Qualification
Product Specification	This document represents the anticipated production performance characteristics of the device.	Production

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